

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

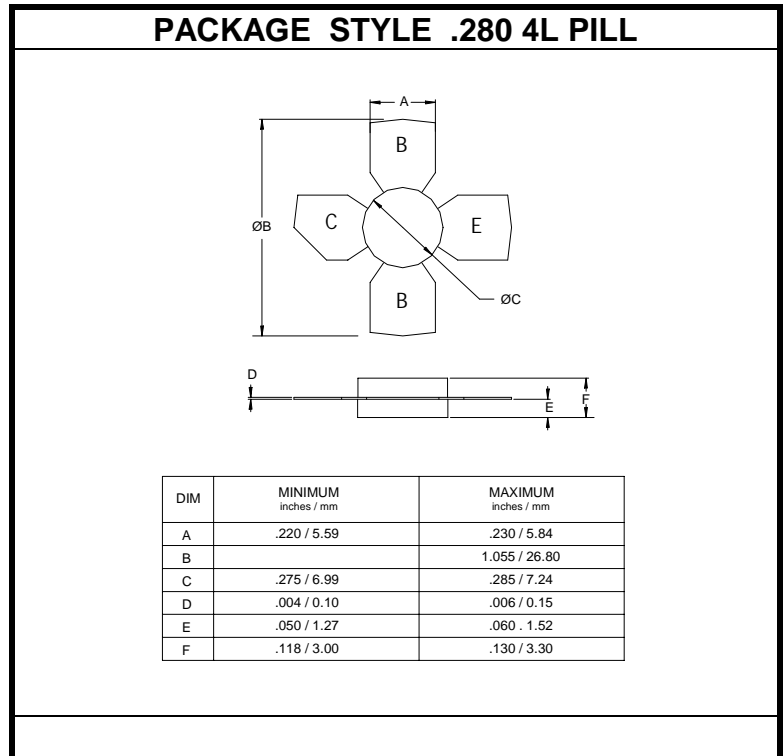
The **ASI MRF1004MB** is Designed for Class B and C, TACAN, IFF, and DME Applications up to 1090 MHz.

**FEATURES:**

- Class B and C Operation
- Common Base
- $P_G = 10$  dB at 4.0 W/1090 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	250 mA
$V_{CE}$	20 V
$P_{DISS}$	7.0 W @ $T_C = 25^\circ\text{C}$
$T_J$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$
$T_{STG}$	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
$\theta_{JC}$	25.0 $^\circ\text{C}/\text{W}$


**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 5.0$ mA	50			V
$BV_{CEO}$	$I_C = 5.0$ mA	20			V
$BV_{EBO}$	$I_E = 1.0$ mA	3.5			V
$I_{CBO}$	$V_{CB} = 35$ V			0.5	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 75$ mA	10		100	---
$P_G$	$V_{CC} = 35$ V $P_{OUT} = 4.0$ W $f = 1090$ MHz	10	11		dB
$\eta_C$		40	45		%